
Processing Materials of 3D Interconnects, Damascene and Electronics Packaging 7

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Table of Contents

<i>Preface</i>	<i>iii</i>
Chapter 1 Device Application, Manufacturing	
Plasma Dicing: Current State & Future Trends <i>R. Westerman, G. Grivna, K. Mackenzie, T. Lazerand, J. Doub</i>	3
Miniaturization and Biocompatible Encapsulation for Implantable Biomedical Silicon Devices <i>J. C. Souriau, J. M. Herrera Morales, L. Castagné, G. Simon, K. Amara, B. Boutaud</i>	15
Chapter 2 Via and Trench Filling - Damascene Process and PCB	
Kinetic on Copper Damascene and Cuprous Concentration Computation in with Cl ⁻ and SPS <i>V. H. Hoang, M. Yokoi, K. Kondo</i>	27
Chapter 3 TSV Filling - Optimal Filling and Evaluation	
Optimizing TSV Fill Phases for Improved Fill Rate, Process Stability and Void Performance <i>J. Ghekiere, R. Mikkola, D. Kebreab, J. Burnham, B. Hoerner, D. Erickson</i>	41

Chapter 4
Cu Electrodeposition - from Fundamentals to Applications

Towards Quantification of Contaminants in Electrodeposited Cu Films <i>N. T. M. Hai, V. Grimaudo, P. Moreno-García, P. Broekmann</i>	57
Dielectric Spectroscopic Detection of Early Failures in 3-D Integrated Circuits <i>Y. S. Obeng, C. A. Okoro, J. J. Ahn, L. You, J. J. Kopanski</i>	69
Combined Surface-Activated Bonding Technique for Low-Temperature Cu/SiO ₂ Hybrid Bonding <i>R. He, M. Fujino, A. Yamauchi, T. Suga</i>	79

Chapter 5
TSV Fabrication - Etching, Dielectric

Electrografted P4VP as Dielectric in High Aspect Ratio TSV: Surface Preparation and Thermomechanical Consideration <i>T. Dequivre, E. Al Alam, J. Plathier, A. Ruediger, G. Brisard, S. Charlebois</i>	91
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Chapter 6
TSV Fabrication - Barrier Layer, Seed Layer

Thermal Decomposition of Tungsten Nitrido Precursors for Low Temperature MOCVD of WN _x C _y <i>S. Y. Kim, A. Koley, R. Bonsu, M. Nolan, L. McElwee-White, T. Anderson</i>	101
Author Index	111